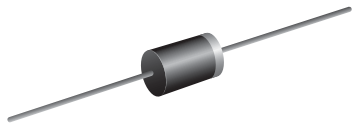
GPP20A - GPP20M

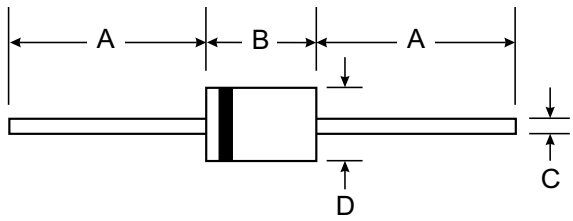
AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V
CURRENT: 2.0 A



Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability



DO-15		
Dim	**Min**	**Max**
A	25.40	—
B	5.50	7.62
C	0.686	0.889
D	2.60	3.60
All Dimensions in mm		

Mechanical Data

- Case: D O - 1 5
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

Maximum Ratings and Electrical Characteristics

T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GPP20A	GPP20B	GPP20D	GPP20G	GPP20J	GPP20K	GPP20M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T_A = 75°C	I_O	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	70							A
Forward Voltage @I_F = 2.0A	V_{FM}	1.0							V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	5.0 50							μA
Typical Junction Capacitance (Note 2)	C_j	20							pF
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	40							K/W
Operating Temperature Range	T_j	-65 to +125							°C
Storage Temperature Range	T_{STG}	-65 to +150							°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

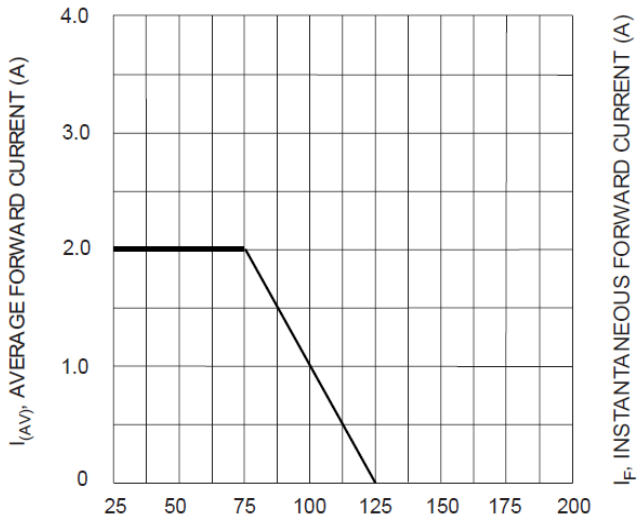


Fig. 1 Forward Current Derating Curve

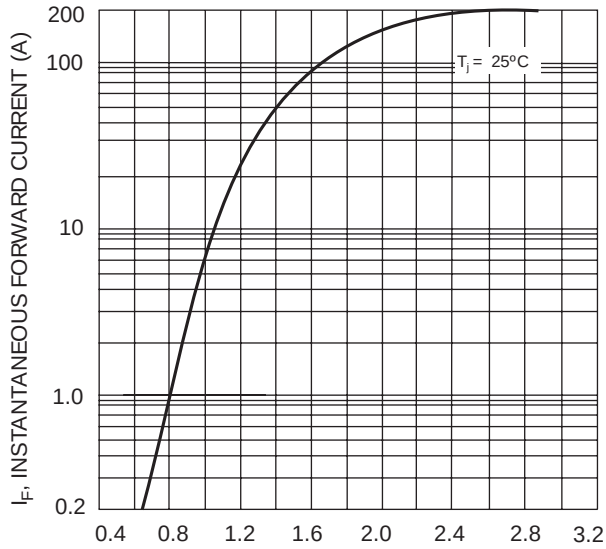


Fig. 2 Typical Forward Characteristics

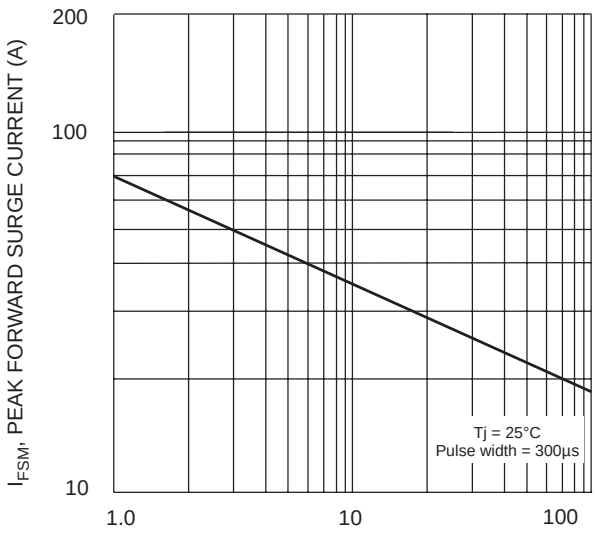


Fig. 3 Maximum Non-Repetitive Surge Current

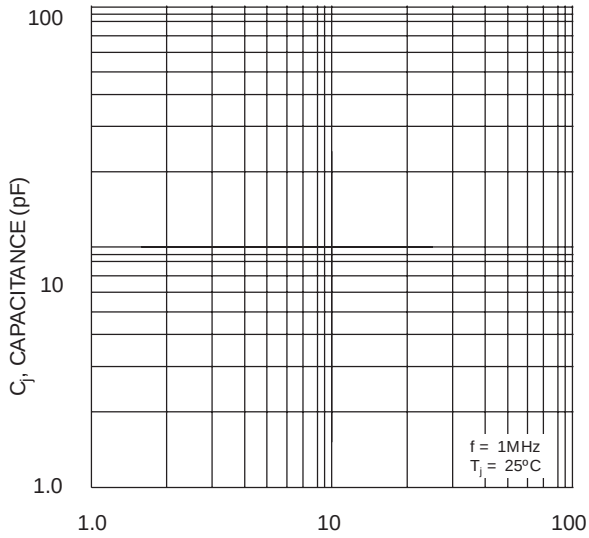


Fig. 4 Typical Junction Capacitance